查询2SC4793供应商 捷多邦，专业PCB打样工厂，24小时加急出货

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE

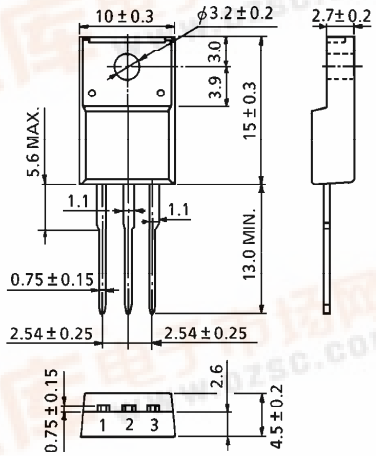
2SC4793

POWER AMPLIFIER APPLICATIONS

DRIVER STAGE AMPLIFIER APPLICATIONS

- High Transition Frequency : f_T = 100MHz (Typ.)
- Complementary to 2SA1837

Unit in mm



1. BASE
2. COLLECTOR
3. EMITTER

JEDEC	—
EIAJ	—
TOSHIBA	2-10R1A

Weight : 1.7g

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	230	V
Collector-Emitter Voltage		V_{CEO}	230	V
Emitter-Base Voltage		V_{EBO}	5	V
Collector Current		I_C	1	A
Base Current		I_B	0.1	A
Collector Power Dissipation	Ta = 25°C	P_C	2.0	W
	Tc = 25°C		20	
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	−55~150	°C

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB} = 230V, I_E = 0	—	—	1.0	μA
Emitter Cut-off Current	I_{EBO}	V_{EB} = 5V, I_C = 0	—	—	1.0	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = 10mA, I_B = 0	230	—	—	V
DC Current Gain	h_{FE}	V_{CE} = 5V, I_C = 100mA	100	—	320	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 500mA, I_B = 50mA	—	—	1.5	V
Base-Emitter Voltage	V_{BE}	V_{CE} = 5V, I_C = 500mA	—	—	1.0	V
Transition Frequency	f_T	V_{CE} = 10V, I_C = 100mA	—	100	—	MHz
Collector Output Capacitance	C_{ob}	V_{CB} = 10V, I_E = 0, f = 1MHz	—	20	—	pF

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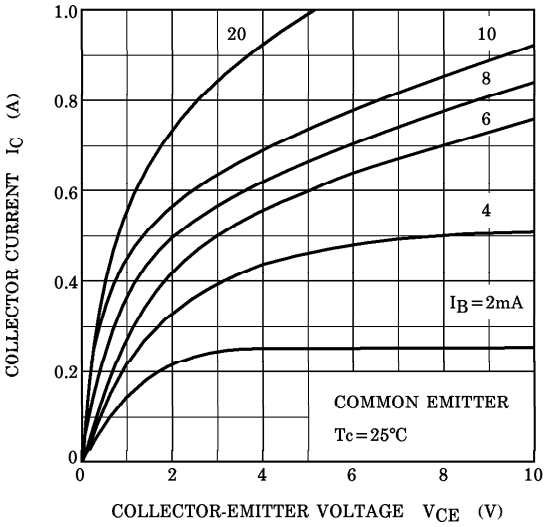
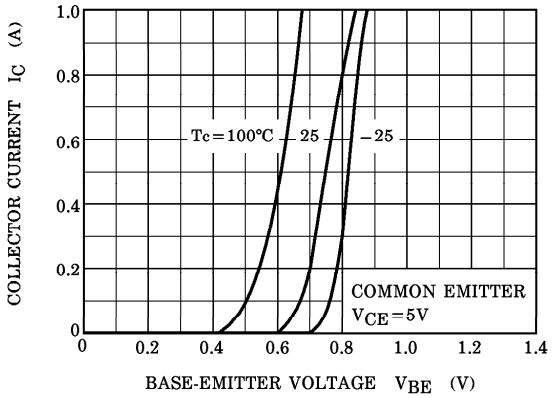
- The information contained herein is subject to change without notice.

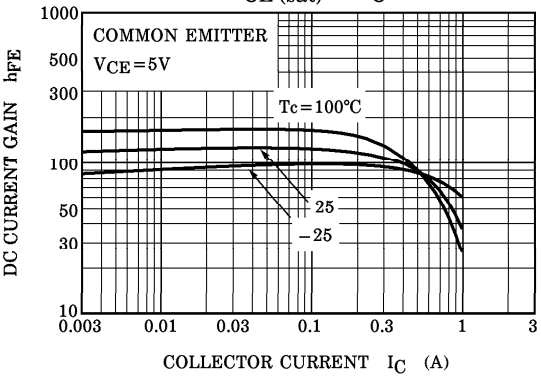
$I_C - V_{CE}$



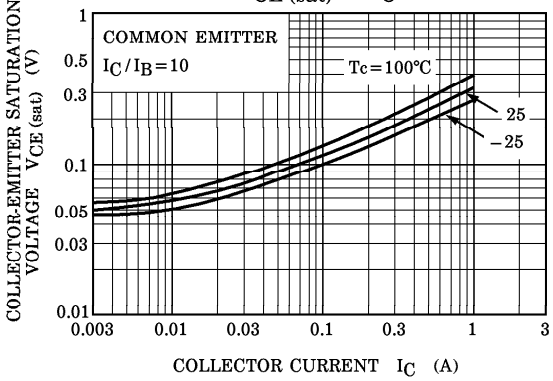
$I_C - V_{BE}$



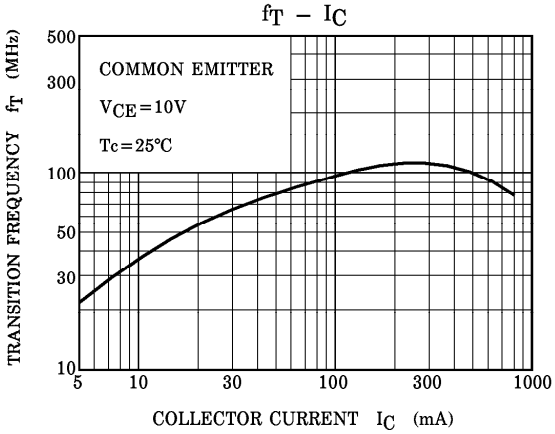
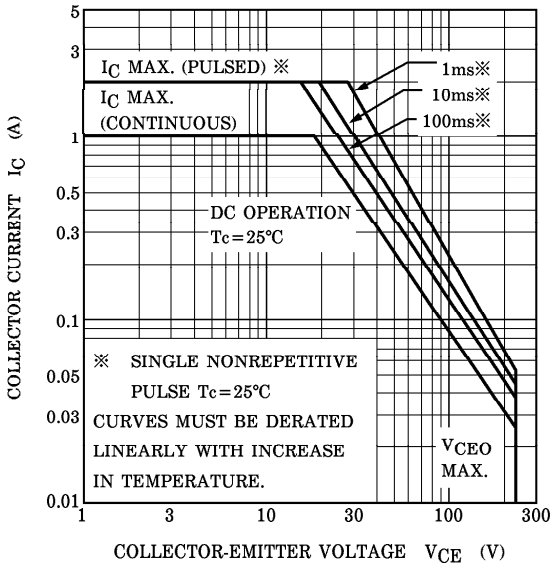
$V_{CE(sat)} - I_C$



$V_{CE(sat)} - I_C$



$f_T - I_C$



SAFE OPERATING AREA